## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

## **Features**

- Low forward voltage
- Allowing high density mounting





SOT-323 Plastic Package Marking Code: YR

## Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	25	V
Reverse Voltage	$V_R$	20	V
Average Forward Current	I <sub>F(AV)</sub>	700	mA
Non-repetitive Peak Forward Surge Current (t = 8.3 ms)	I <sub>FSM</sub>	2	А
Junction Temperature	TJ	125	°C
Storage Temperature Range	Ts	- 55 to + 125	°C

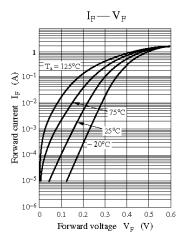
## Characteristics at T<sub>a</sub> = 25 °C

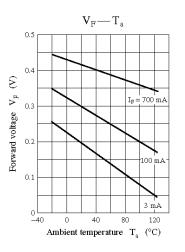
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 700 \text{ mA}$	V <sub>F</sub>	-	0.45	V
Reverse Current at $V_R = 20 \text{ V}$	I <sub>R</sub>	-	200	μΑ
Reverse Breakdown Voltage at $I_R = 600 \mu A$	$V_{(BR)R}$	25	-	V
Junction Capacitance at $V_R = 0$ , $f = 1$ MHz	CJ	-	100	pF

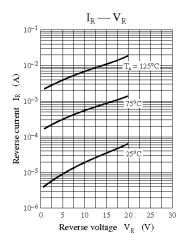


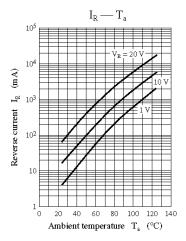


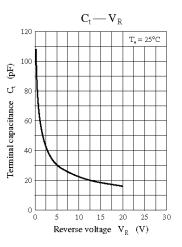
















(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







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